

ABSTRACT OF THE DISCLOSURE

In a process for manufacturing a semiconductor integrated circuit device having a MISFET, in order that a shallow junction between the source/drain of the MISFET and a semiconductor substrate may be realized by reducing the number of heat treatment steps, all conductive films to be deposited on the semiconductor substrate are deposited at a temperature of 500°C or lower at a step after the MISFET has been formed. Moreover, all insulating films to be deposited over the semiconductor substrate are deposited at a temperature of 500°C or lower at a step after the MISFET has been formed.